

ABSTRACT OF THE DISCLOSURE

The present invention relates to a film forming method of forming an interlayer insulating film having a low dielectric constant to cover a wiring. In construction, an insulating film for covering a wiring is formed on the substrate by plasmanizing a film forming gas, that consists of any one selected from a group consisting of alkoxy compound having Si-H bonds and siloxane having Si-H bonds and any one oxygen-containing gas selected from a group consisting of  $O_2$ ,  $N_2O$ ,  $NO_2$ ,  $CO$ ,  $CO_2$ , and  $H_2O$ , to react.